



Attorney's Docket No. 5308-156

2811
PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re: Ryu et al.
Serial No.: 09/911,995
Filed: July 24, 2001

Group Art Unit: 2811
Confirmation No.: 5240
Examiner: Gene M. Munson

For: SILICON CARBIDE POWER METAL-OXIDE SEMICONDUCTOR FIELD
EFFECT TRANSISTORS HAVING A SHORTING CHANNEL AND
METHODS OF FABRICATING SILICON CARBIDE METAL-OXIDE
SEMICONDUCTOR FIELD EFFECT TRANSISTORS HAVING A
SHORTING CHANNEL

Date: January 20, 2004

Commissioner for Patents
PO Box 1450
Alexandria, VA 22313

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

Sir:

Attached is a list of documents on form PTO-1449 together with copies of each identified document. This Information Disclosure Statement is submitted in accordance with 37 C.F.R. § 1.97(c), before final Office Action or Allowance, whichever is earlier.

Please find attached a check in the amount of \$180.00 for the fee specified in 37 C.F.R. § 1.17(p). The Commissioner is authorized to charge any additional fee or credit any refund to Deposit Account No. 50-0220.

Respectfully submitted,

Elizabeth A. Stanek
Registration No. 48,568

Customer No. 20792
Myers Bigel Sibley & Sajovec
P. O. Box 37428
Raleigh, North Carolina 27627
Telephone: (919) 854-1400
Facsimile: (919) 854-1401

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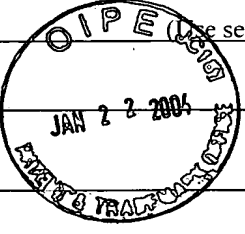
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FORM PTO-1449 U.S. Department of Commerce Patent and Trademark Office LIST OF DOCUMENTS CITED BY APPLICANT (Use several sheets if necessary)				Attorney Docket Number 5308-156		Serial No. 09/911,995	
				Applicants: Ryu et al.			
				Filing Date: July 24, 2001		Group 2811	
U. S. PATENT DOCUMENTS							
Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate
	1	5,479,316	12/26/95	Smrtic et al.	361	322	
	2	5,739,564	04/14/98	Kosa et al.	257	298	
	3	6,228,720	05/08/01	Kitabatake et al.	438	268	
	4	6,239,463	05/29/01	Williams et al.	257	328	
	5	6,316,791	11/13/01	Schörner et al.	257	77	
	6	6,593,620	07/15/03	Hshieh et al.	257	335	
	7	6,610,366	08/26/03	Lipkin	427	378	
FOREIGN PATENT DOCUMENTS							
		Document Number	Date	Country	Class	Subclass	Translation Yes No
	8	WO98/02924	01/22/98	PCT			
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)							
	9	Dimitrijevic et al., "Nitridation of Silicon-Dioxide Films Grown on 6H Silicon Carbide", <i>IEEE Electronic Device Letters</i> , Vol. 18, No. 5, May 05, 1997, pp. 175-177.					
	10	De Mao et al., "Thermal Oxidation of SiC in N ₂ O", <i>J. Electrochem. Soc.</i> , Vol. 141, 1994, pp. L150-L152.					
	11	Ryu et al., Article and Presentation: "27 mΩ-cm ² , 1.6 kV Power DiMOSFETs in 4H-SiC," <i>Proceedings of the 14 International Symposium on Power Semiconductor Devices & ICs 2002</i> , June 4-7, 2002, Santa Fe, NM.					
	12	Kobayashi et al. "Dielectric Breakdown and Current Conduction of Oxide/Nitride/Oxide Multi-Layer Structures," <i>1990 IEEE Symposium on VLSI Technology</i> . pp. 119-120.					
	13	Ma et al. "Fixed and trapped charges at oxide-nitride-oxide heterostructure interfaces formed by remote plasma enhanced chemical vapor deposition," <i>J. Vac. Sci. Technol. B</i> . Vol. 11, No. 4, Jul/Aug 1993, pp. 1533-40.					

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DATE CONSIDERED

Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.